

NEC

HIGH ISOLATION VOLTAGE DARLINGTON TRANSISTOR TYPE MULTI OPTOCOUPLER SERIES

PS2502 -1, -2, -4
PS2502L -1, -2, -4

FEATURES

- **HIGH ISOLATION VOLTAGE**
BV: 5 k V_{r.m.s.} MIN
- **HIGH CURRENT TRANSFER RATIO**
CTR: 2000% TYP
- **HIGH SPEED SWITCHING**
tr, tf = 100 μs TYP
- **LOW COST**
- **ISOLATED CHANNELS PER EACH PACKAGE**

DESCRIPTION

PS2502-1, -2, -4 and PS2502L-1, -2, -4 are optically coupled isolators containing a GaAs light emitting diode and an NPN silicon Darlington phototransistor. PS2502-1, -2, and -4 are in a plastic DIP (Dual In-line Package) and PS2502L-1, -2, and -4 are lead bending type (Gull-wing) for surface mount.

APPLICATIONS

Interface circuit for various instrumentations and control equipment.

- AC LINE / DIGITAL LOGIC
- DIGITAL LOGIC / DIGITAL LOGIC
- TWISTED PAIR LINE RECEIVER
- TELEPHONE / TELEGRAPH LINE RECEIVER
- HIGH FREQUENCY POWER SUPPLY
FEEDBACK CONTROL
- RELAY CONTACT MONITOR
- POWER SUPPLY MONITOR

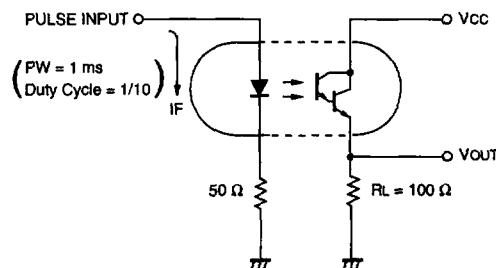
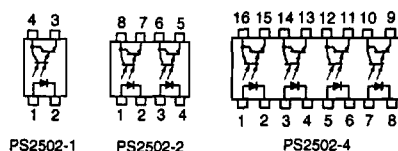
ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

PART NUMBER				PS2502-1, -2, -4, PS2502L-1, -2, -4		
SYMBOLS		PARAMETERS	UNITS	MIN	TYP	MAX
Diode	V _F	Forward Voltage, I _F = 10 mA	V		1.17	1.4
	I _R	Reverse Current, V _R = 5 V	μA			5
	C	Junction Capacitance, V = 0, f = 1.0 MHz	pF		50	
Transistor	I _{CEO}	Collector to Emitter Dark Current, V _{CE} = 40 V, I _F = 0	nA			400
	BV _{CEO}	Collector to Emitter Breakdown Voltage, I _C = 1 mA, I _B = 0	V	40	60	
	BV _{ECO}	Emitter to Collector Breakdown Voltage, I _E = 100 μA, I _B = 0	V	6	8	
Coupled	CTR	Current Transfer Ratio ¹ , I _F = 1 mA, V _{CE} = 2 V	%	200	2000	
	V _{CE(sat)}	Collector Saturation Voltage, I _F = 1 mA, I _C = 2 mA	V			1.0
	R ₁₋₂	Isolation Resistance, V _{in-out} = 1.0 kV	Ω	10 ¹¹		
	C ₁₋₂	Isolation Capacitance, V = 0, f = 1.0 MHz	pF		0.5	
	t _r	Rise Time ² , V _{CC} = 10 V, I _C = 10 mA, R _L = 100 Ω	μs		100	
	t _f	Fall Time ² , V _{CC} = 10 V, I _C = 10 mA, R _L = 100 Ω	μs		100	

Notes:

1. CTR rank (PS2502-1, PS2502L-1 only)
K: 2000 %
L: 700 to 3400 %
M: 200 to 1000 %

2. Test Circuit for Switching Time



PS2502- 1, -2, -4, PS2502L -1, -2, -4

ABSOLUTE MAXIMUM RATINGS¹ (T_A = 25°C)

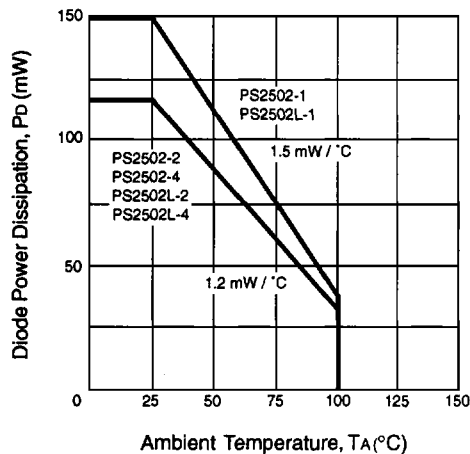
SYMBOLS	PARAMETERS	UNITS	RATINGS	
			PS2502 -1 PS2502L-1	PS2502 -2, 4 PS2502L-2, 4
Diode				
I _F	Forward Current	mA	80	80
V _R	Reverse Voltage	V	6	6
P _D	Power Dissipation	mW/ch	150	120
I _F (PEAK)	Peak Forward Current (PW = 100 μs, Duty Cycle 1%)	A	1	1
Transistor				
V _{CEO}	Collector to Emitter Voltage	V	40	40
V _{ECO}	Emitter to Collector Voltage	V	6	6
I _C	Collector Current	mA	200	160
P _C	Power Dissipation	mW/ch	200	160
Coupled				
BV	Isolation Voltage ²	V _{r.m.s.}	5000	5000
T _{stg}	Storage Temperature	°C	-55 to +150	-55 to +150
T _{opt}	Operating Temperature	°C	-55 to +100	-55 to +100
T _{sol}	Lead Temperature (Soldering 10 s)	°C	260	260
P _T	Total Power Dissipation	mW/ch	250	200

Notes:

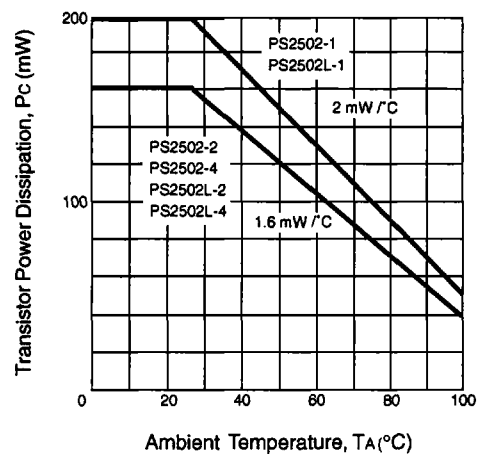
1. Operation in excess of any one of these parameters may result in permanent damage.
2. AC voltage for 1 minute at T_A = 25 °C, RH = 60 % between input and output.

TYPICAL PERFORMANCE CURVES (T_A = 25 °C)

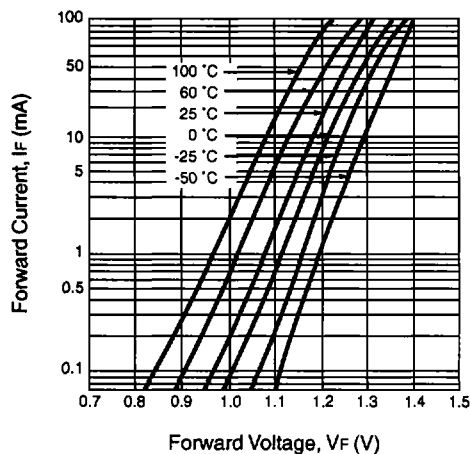
DIODE POWER DISSIPATION vs.
AMBIENT TEMPERATURE



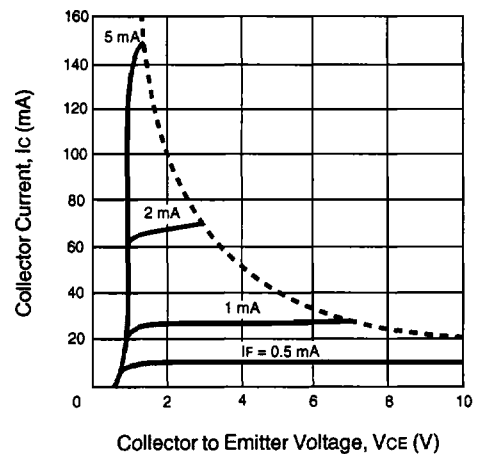
TRANSISTOR POWER DISSIPATION
vs. AMBIENT TEMPERATURE

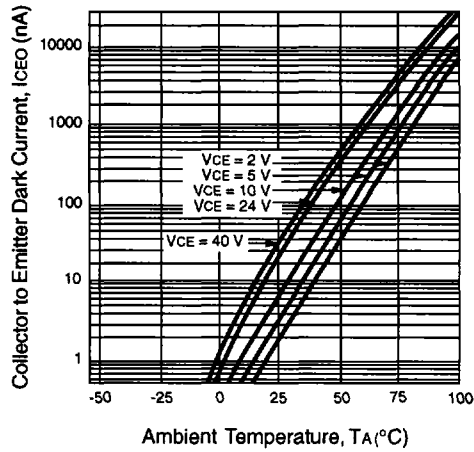
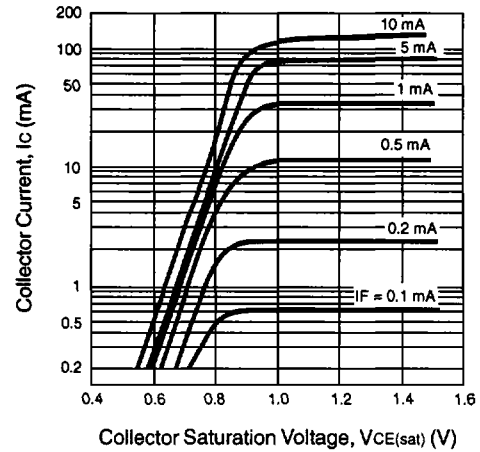
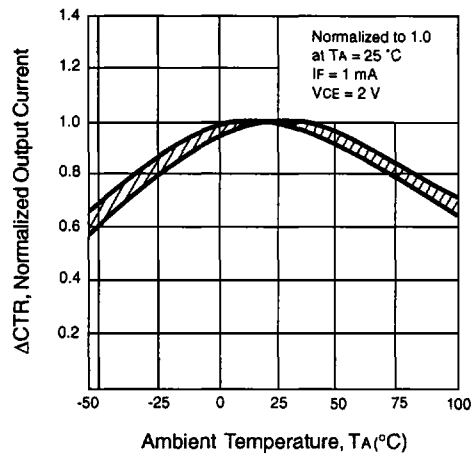
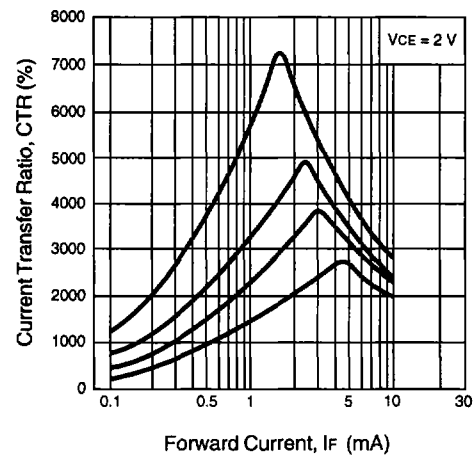
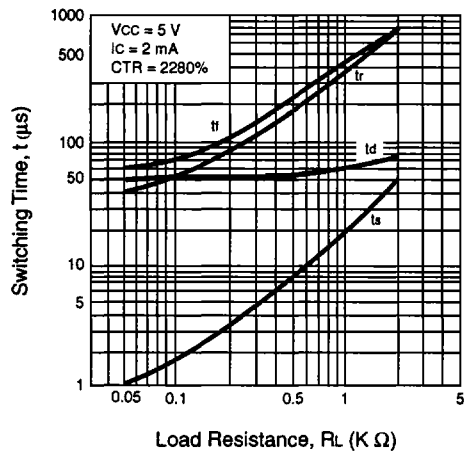
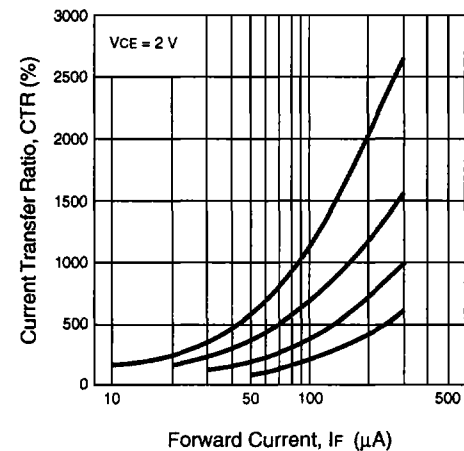


FORWARD CURRENT vs.
FORWARD VOLTAGE

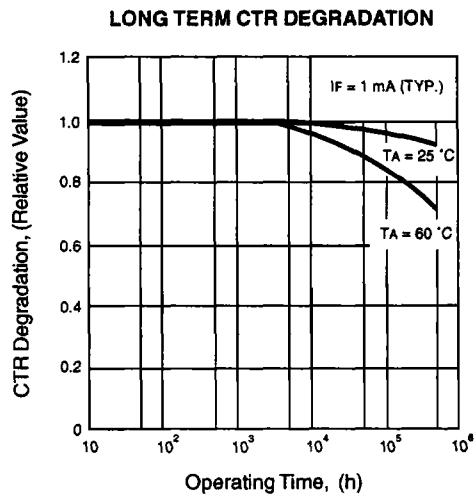
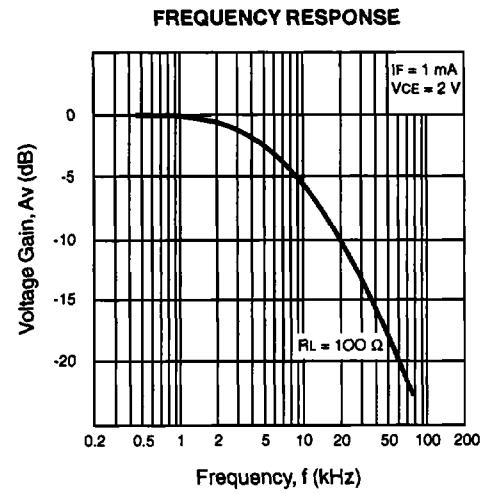
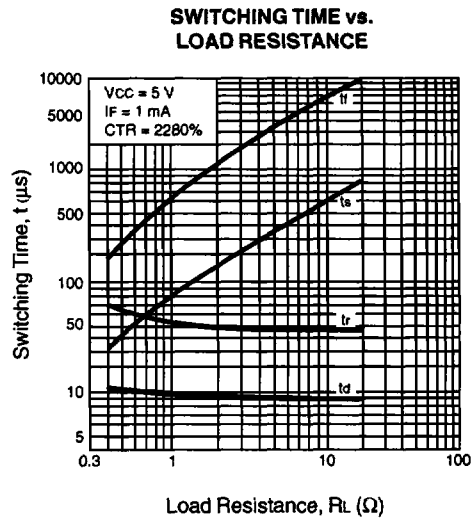


COLLECTOR CURRENT vs.
COLLECTOR to EMITTER VOLTAGE

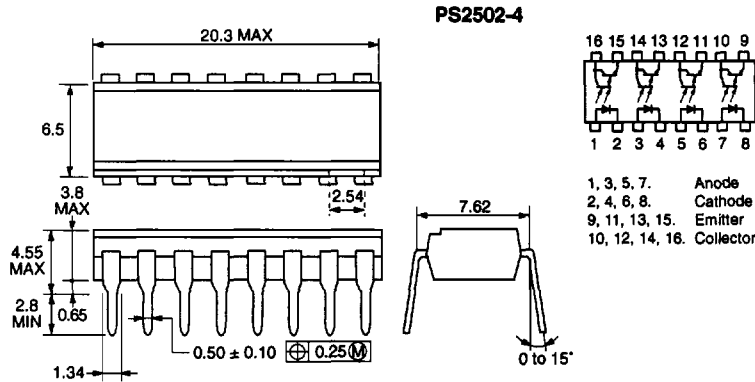
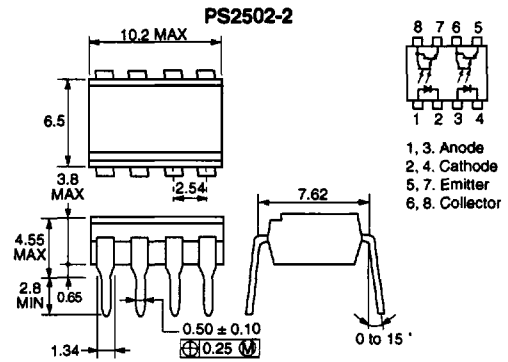
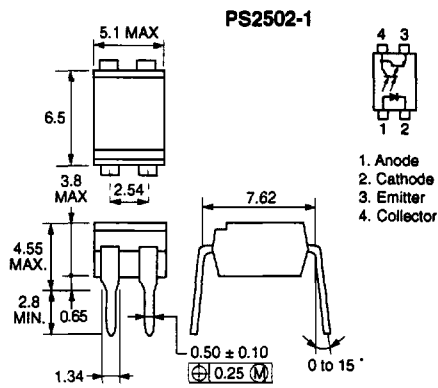


TYPICAL PERFORMANCE CURVES ($T_A = 25^\circ\text{C}$)**COLLECTOR TO EMITTER DARK CURRENT vs. AMBIENT TEMPERATURE****COLLECTOR CURRENT vs. COLLECTOR SATURATION VOLTAGE****NORMALIZED OUTPUT CURRENT vs. AMBIENT TEMPERATURE****CURRENT TRANSFER RATIO vs. FORWARD CURRENT****SWITCHING TIME vs. LOAD RESISTANCE****CURRENT TRANSFER RATIO vs. FORWARD CURRENT**

TYPICAL PERFORMANCE CURVES (T_A = 25 °C)



OUTLINE DIMENSIONS (Units in mm) DIP (Dual In-Line Package)



OUTLINE DIMENSIONS (Units in mm) Lead Bending type (Gull-wing)

